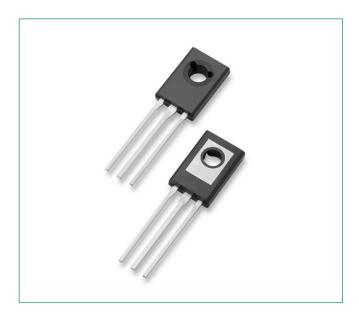


T2322B





Description

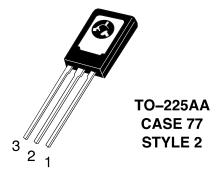
Designed primarily for ac power switching. The gate sensitivity of these triacs permits the use of economical transistorized or integrated circuit control circuits, and it enhances their use in low-power phase control and load-switching applications.

Features

- Very High Gate Sensitivity
- Low On-State Voltage at High Current Levels
- Glass-Passivated Chip for Stability
- Small, Rugged Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability

 Pb–Free Package is Available

Pin Out



Functional Diagram



Additional Information







Samples

Thyristors Surface Mount - 200V > T2322B

Maximum Ratings (T _J = 25°C unless otherwise noted)						
Rating	Symbol	Value	Unit			
Peak Repetitive Off-State Voltage (Note 1) (T _J = 25 to 110°C, Gate Open)	V _{DRM} , V _{RRM}	200	V			
On-State RMS Current $(T_c = 70^{\circ}C)$ (Full Cycle Sine Wave 50 to 60 Hz)	I _{T (RMS)}	2.5	А			
Peak Non–Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_c = 70^{\circ}$ C)	I _{TSM}	25	А			
Circuit Fusing Considerations (t = 8.3 ms)	l²t	2.6	A2s			
Peak Gate Power (Pulse Width \leq 10 sec, $T_C = 70$ °C)	P _{GM}	10	W			
Average Gate Power (t = 8.3 msec, $T_A = 25^{\circ}C$)	P _{GM (AV)}	0.5	W			
Peak Gate Current (Pulse Width = 10 μs, T _C = 70°C)	I _{GM}	0.5	Α			
Operating Junction Temperature Range @ Rated $V_{\scriptscriptstyle RRM}$ and $V_{\scriptscriptstyle DRM}$	T,	-40 to +110	°C			
Storage Temperature Range	T _{stg}	-40 to +150	°C			
Mounting Torque (6-32 Screw) (Note 2)	_	8.0	in. lb.			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient PCB Mounted	R _{eJA}	3.5	°C/W
Thermal Resistance, Junction-to-Tab Measured on MT2 Tab Adjacent to Epoxy	R _{eJT}	60	°C/W
Maximum Device Temperature for Soldering Purposes for 10 Secs Maximum	T _L	260	°C

Electrical Characteristics - **OFF** (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Forward or Reverse Blocking Current	T, = 25°C	DRM'	-	-	1.0	m A
$(V_D = Rated V_{DRM} and V_{RRM}; Gate Open)$	J J DRIVI' I		-	0.2	0.75	mA

Electrical Characteristics - ON $(T_J = 25^{\circ}\text{C unless otherwise noted}; Electricals apply in both directions)$

Characteristic		Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 3) ($I_{TM} = \pm 10 \text{ A}$)	V _{TM}	-	1.7	2.2	V
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, R_L = 100 \Omega, \text{ All Quadrants})$		-	_	10	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_C = 25^{\circ}\text{C})$		-	1.0	2.2	V
Gate Non-Trigger Voltage $(V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_C = 110^{\circ}\text{C})$		0.15	_	_	V
Holding Current (VD = 12 V, IT (Initiating Current) = ±200 mA, Gate Open)		-	15	30	mA
Gate Controlled Turn-On Time ($V_D = Rated V_{DRM'} I_{TM} = 10 A pk, I_G = 60 mA, tr = 0.1 sec)$		_	1.8	2.5	μs

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} Torque rating applies with use of torque washer (Shakeproof WD19523 or equivalent). Mounting Torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Main terminal 2 and heat-sink contact pad are common.

Dynamic (Characteristics
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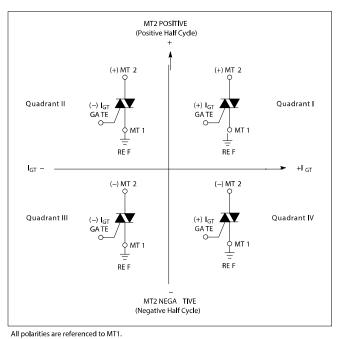
Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Off State Voltage $(V_D = Rated V_{DRM'} Exponential Waveform, T_C = 100°C)$	dv/dt	10	100	-	V/µs
Critical Rate of Rise of On–State Current (V_D = Rated $V_{DRM'}$ I_{TM} = 3.5 A pk, Commutating di/dt = 1.26 A/ms, Gate Unenergized, T_C = 90°C)	di/dt	1.0	4.0	-	A/µs

^{2.} Pulse Width =1.0 ms, Duty Cycle \leq 1%.

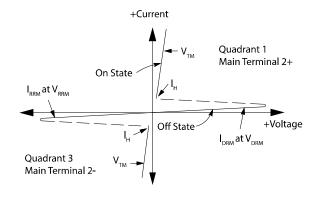
Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac

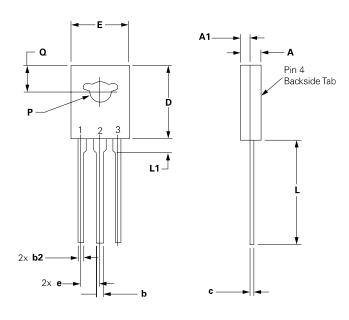


With in—phase signals (using standard AC lines) quadrants I and III are used

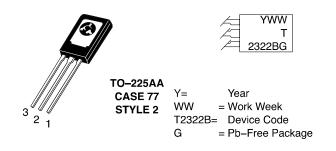




Dimensions



Part Marking System



Pin Assignment				
1	Cathode			
2	Anode			
3	Gate			
4	Anode			

Dim	Inc	hes	Millimeters		
Dilli	Min	Max	Min	Max	
А	0.102	0.110	2.60	2.80	
A1	0.047	0.055	1.20	1.40	
b	0.028	0.034	0.70	0.86	
b2	0.028	0.034	0.70	0.86	
С	0.019	0.022	0.49	0.57	
D	0.417	0.449	10.60	11.40	
E	0.291	0.323	7.40	8.20	
е	0.090 TYP		2.29TYP		
L	0.551	0.630	14.00	16.00	
L1	0.091	0.106	2.30	2.70	
Р	0.118	0.134	3.00	3.40	
Q	0.142	0.157	3.60	4.00	

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

Ordering Information Device Package **Shipping** T2322B TO225AA 500 Units/Box TO225AA T2322BG (Pb-Free)

^{2.} CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.